/ Descriptions

WR0553I ṂṂ Ł QSQ ÆṀ ɥ s ǁ ˥ Silicon NPN transistor in a TO-220F Plastic Package.

/ Features

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High voltage high speed switching.

/ Applications

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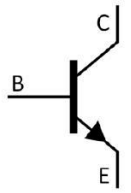
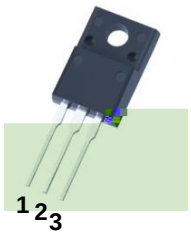
Switching regulator applications, High voltage switching applications, High speed DC-DC converter applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

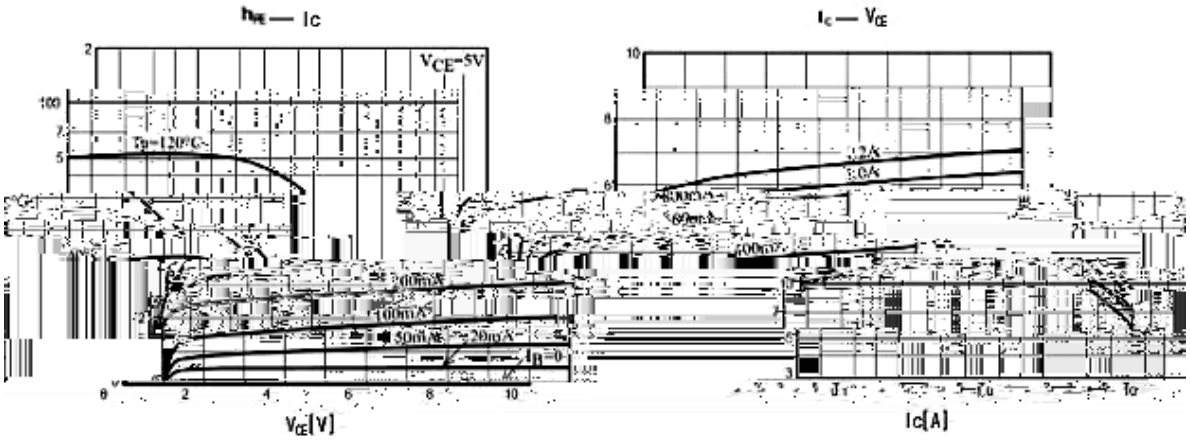
/ h_{FE} Classifications & Marking

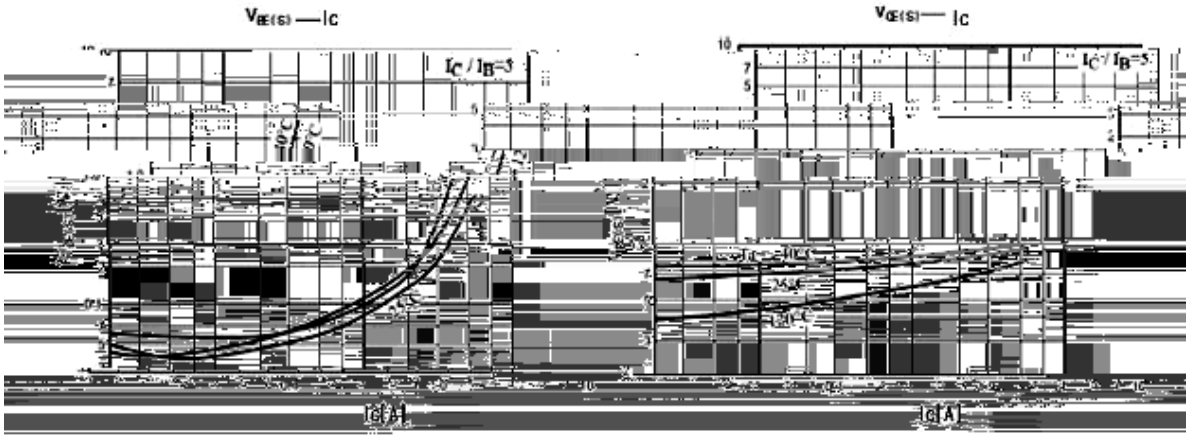
ð м ˥ ب ˝ See Marking Instructions .

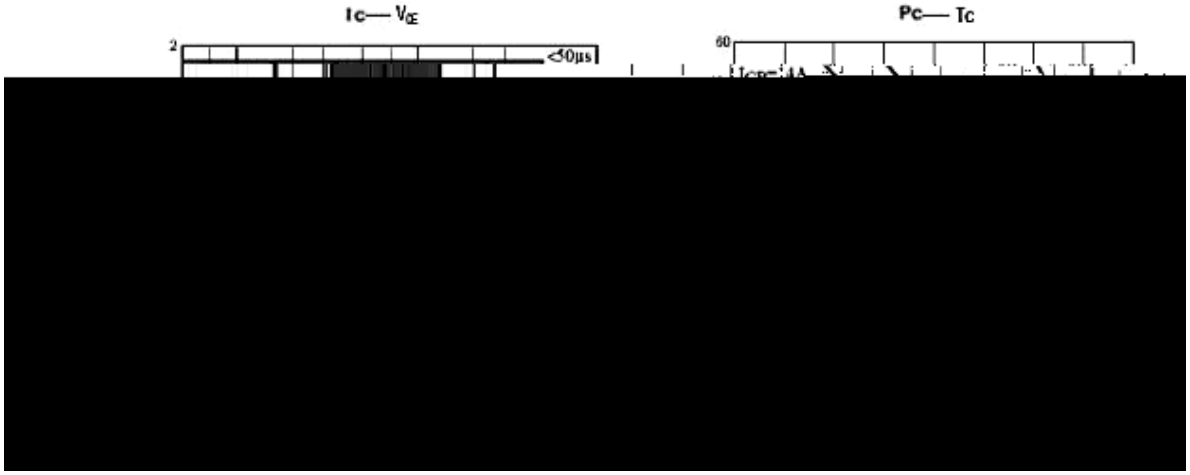
v ̈Ω Parameter	ϟ N Symbol	̈Ω Ö Rating	D Ӈ Unit
Collector to Base Voltage	V_{CBO}	900	V
Collector to Emitter Voltage	V_{CEO}	500	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	7.0	A
Peak Collector Current	I_{cm}	14	A
Collector Power Dissipation	P_C(Tc=25)	45	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̈Ω Parameter	ϟ N Symbol	⊥⊥ ;ˣ Ţ Test Conditions	ω ṇ Ö Min	Ɛ ʒ Ö Typ	ω ᶻ Ö Max	D Ӈ Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=1mA I_B=0	900			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=10mA I_B=0	500			V
Collector Cut-Off Current	I_{CEO}	V_{CE}=500V I_E=0			250	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5V I_C=0			10	μA

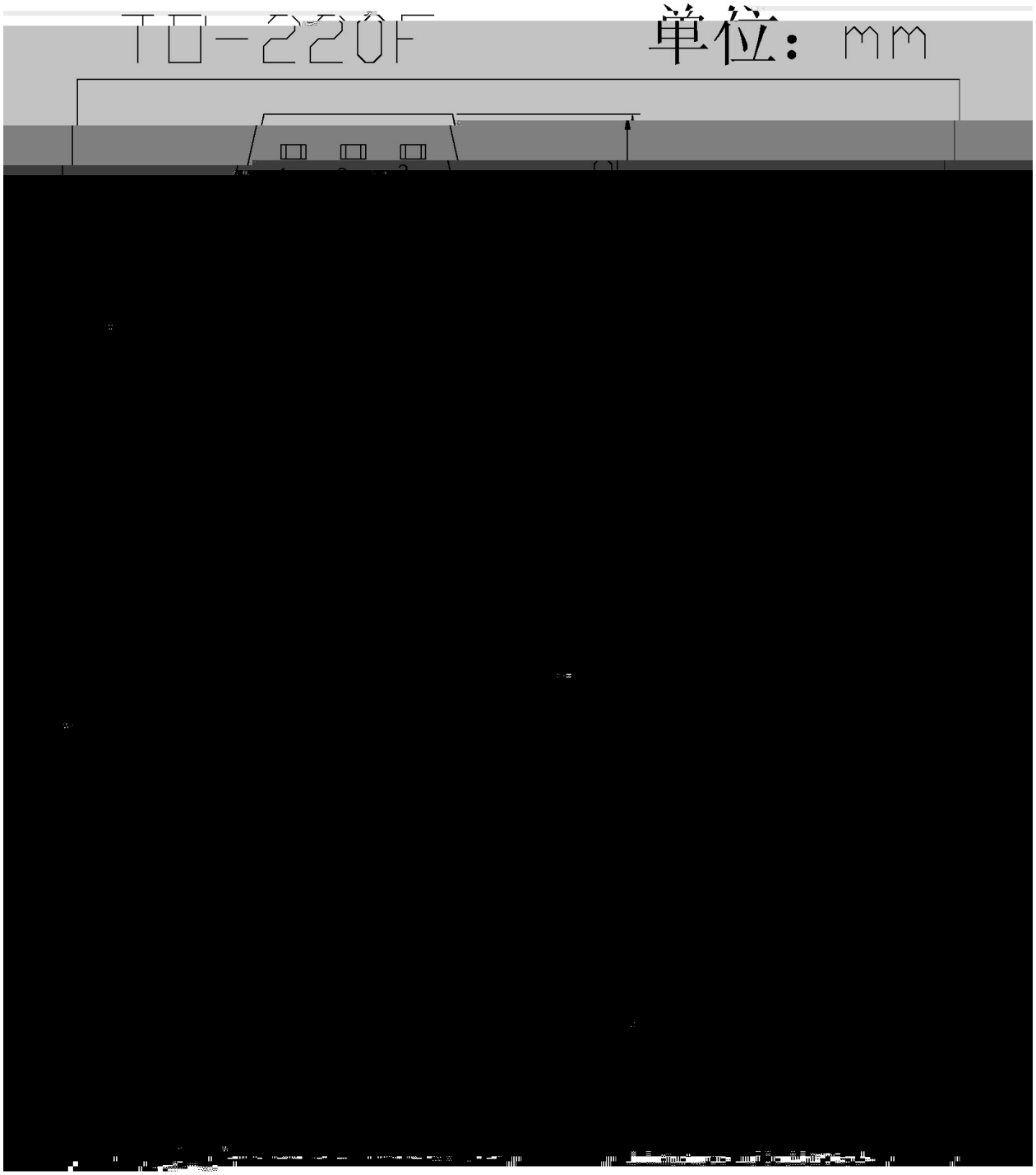
/ Electrical Characteristic Curve







/ Package Dimensions



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